

*Last search for paper no. 0105*

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4602	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing)	USPAT	OR	OFF	2005/01/21 10:38
S2	34	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing) with determined	USPAT	OR	OFF	2005/01/19 12:06
S3	1128	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate)	USPAT	OR	OFF	2005/01/19 12:06
S4	470	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with surface	USPAT	OR	OFF	2005/01/19 12:06
S5	63	(removed) with thickness with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with surface	USPAT	OR	OFF	2005/01/19 12:10
S6	0	(removed) with thickness with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with surface with roughness	USPAT	OR	OFF	2005/01/19 12:11
S7	5	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with surface with roughness	USPAT	OR	OFF	2005/01/19 12:13
S8	1	(removed) with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with surface with roughness	USPAT	OR	OFF	2005/01/19 12:13
S9	5	(removed) with layer with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with roughness	USPAT	OR	OFF	2005/01/19 12:14
S10	0	S9 not S7	USPAT	OR	OFF	2005/01/19 12:14
S11	2	(removed) with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with roughness	USPAT	OR	OFF	2005/01/19 13:46
S12	0	(removed) with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with topography	USPAT	OR	OFF	2005/01/19 13:47

S13	0	(removed) with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with topography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:47
S14	3	(removed) with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with planarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:50
S15	0	determined with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with planarity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:50
S16	110	determined with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:53
S17	3	determined with thickness with (cmp (touch with (smoothing polishing)) polishing) with (silicon substrate) with roughness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:53
S18	62	S16 and ("438"/\$3 "257"/\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 13:54
S19	21	oxidizing same deoxidizing same (hydrogen reductive)	USPAT	OR	OFF	2005/01/21 10:40
S20	2	oxidizing same deoxidizing same (hydrogen reductive) same annealing	USPAT	OR	OFF	2005/01/21 10:39
S21	2	S19 and semiconductor	USPAT	OR	OFF	2005/01/21 10:46
S22	1	pre-smoothing and (polishing cmp)	USPAT	OR	OFF	2005/01/21 10:47
S23	1	pre-smooth and (polishing cmp)	USPAT	OR	OFF	2005/01/21 10:47
S24	0	S23 not S22	USPAT	OR	OFF	2005/01/21 10:47
S25	1	pre-smoothing and semiconductor	USPAT	OR	OFF	2005/01/21 10:47
S26	0	S25 not S23	USPAT	OR	OFF	2005/01/21 10:47
S27	1	pre-smoothing and substrate	USPAT	OR	OFF	2005/01/21 10:48

S28	1280	smoothing same (polishing cmp)	USPAT	OR	OFF	2005/01/21 10:48
S29	1018	smoothing with (polishing cmp)	USPAT	OR	OFF	2005/01/21 10:48
S30	31	smoothing with (polishing cmp) same hydrogen	USPAT	OR	OFF	2005/01/21 10:48
S31	15	smoothing with (polishing cmp) with hydrogen	USPAT	OR	OFF	2005/01/21 10:50
S32	17	S30 and oxidizing	USPAT	OR	OFF	2005/01/21 10:50